

UNISONIC TECHNOLOGIES CO., LTD

60N15 Preliminary Power MOSFET

60A, 150V N-CHANNEL POWER MOSFET

■ DESCRIPTION

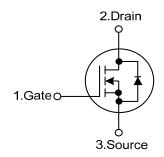
The UTC **60N15** is an N-channel power MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$, high switching speed, high current capacity and low gate charge.

The UTC **60N15** is suitable for motor control, AC-DC or DC-DC converters and audio amplifiers, etc.

■ FEATURES

- * $R_{DS(ON)}$ <30m Ω @ V_{GS} =10V, I_D =30A
- * High Switching Speed
- * High Current Capacity
- * Low Gate Charge(typical 130nC)

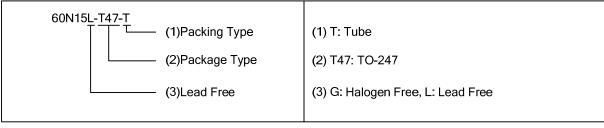
■ SYMBOL

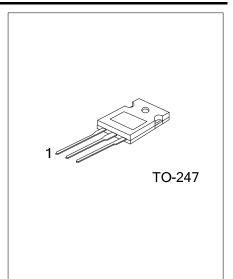


ORDERING INFORMATION

Ordering Number		Dookona	Pin Assignment			Daaldaa	
Lead Free	Halogen Free	Package	1	2	3	Packing	
60N15L-T47-T	60N15G- T47-T	TO-247	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source





■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage (V _{GS} =0)		V_{DSS}	150	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Drain Current	Continuous	I_D	60	Α	
	Pulsed (Note 1)	I_{DM}	240	Α	
Avalanche Current		I _{AR}	60	Α	
Avalanche Energy		E _{AS}	1000	mJ	
Power Dissipation		P _D	125	W	
Junction Temperature		TJ	150	°C	
Storage Temperature		T _{STG}	-55 ~ + 150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse width limited by safe operating area

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	°C/W
Junction to Case	$\theta_{ m JC}$	1	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS	•			•				
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V				٧	
Drain-Source Leakage Current		I _{DSS}	V _{DS} =150V, V _{GS} =0V			1	μΑ	
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+20V, V _{DS} =0V			+100	nA	
	Reverse		V _{GS} =-20V, V _{DS} =0V			-100	nA	
ON CHARACTERISTICS (Note 2)								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2	3	4	٧	
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =30A			30	mΩ	
DYNAMIC PARAMETERS								
nput Capacitance		C_{ISS}			3900		pF	
Output Capacitance		Coss	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		950		pF	
Reverse Transfer Capacitance		C_{RSS}			250		pF	
SWITCHING PARAMETERS								
Total Gate Charge		Q_G			130	170	nC	
Gate to Source Charge		Q_GS	V_{GS} =10V, V_{DD} =75V, I_{D} =60A		26		nC	
Gate to Drain Charge		Q_GD			55		nC	
Turn-ON Delay Time		$t_{D(ON)}$			30		ns	
Rise Time		t_R	V_{DD} =30V, I_{D} =60A, R_{G} =4.7 Ω ,		180		ns	
Fall-Time		t_{F}	V _{GS} =10V		35		ns	
Off-Voltage Rise Time		$t_{R(OFF)}$			135		ns	
SOURCE- DRAIN DIODE RATI	NGS AND (CHARACTER	RISTICS					
Maximum Body-Diode Continuous Current		Is	(Note 1)			60	Α	
Maximum Body-Diode Pulsed Current		I_{SM}				240	Α	
Drain-Source Diode Forward Voltage		V_{SD}	I _{SD} =60A, V _{GS} =0V (Note 2)			1.6	V	

Notes: 1. Pulse width limited by safe operating area

2. Pulsed: Pulse duration=300µs, Duty cycle 1.5%

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